

# Phototransistor, top view type

## RPT-34PB3F

The RPT-34PB3F is a silicon planar phototransistor.  
It is particularly suited for use with a ROHM SIR-34ST3F infrared light emitting diode.

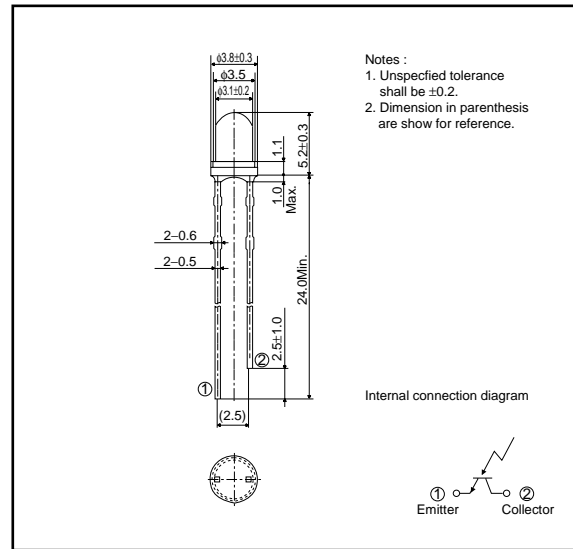
●Applications

Optical control equipment

●Features

High sensitivity.

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-emitter voltage	V <sub>CEO</sub>	32	V
Emitter-collector voltage	V <sub>ECO</sub>	5	V
Collector current	I <sub>C</sub>	30	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Operating temperature	T <sub>opr</sub>	-25~+85	°C
Storage temperature	T <sub>stg</sub>	-30~+100	°C

●Electrical and optical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Light current	I <sub>C</sub>	2.0	-	-	mA	V <sub>CE</sub> =5V, E=500Lx
Dark current	I <sub>CEO</sub>	-	-	0.5	μA	V <sub>CE</sub> =10V(Black box)
Peak sensitivity wavelength	λ <sub>P</sub>	-	800	-	nm	-
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	-	0.4	V	I <sub>C</sub> =1mA, E=500Lx
Half-angle	θ <sub>1/2</sub>	-	±36	-	deg	-
Response time	t <sub>r</sub> -t <sub>f</sub>	-	10	-	μs	V <sub>CC</sub> =5V, I <sub>C</sub> =1mA, R <sub>L</sub> =100Ω

Sensors

●Electrical and optical characteristic curves

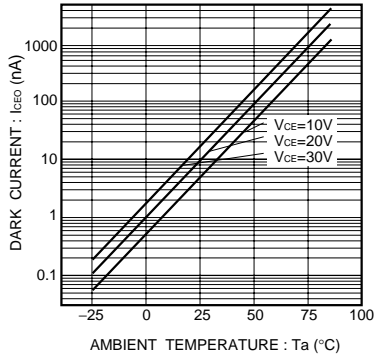


Fig.1 Dark current vs. ambient temperature

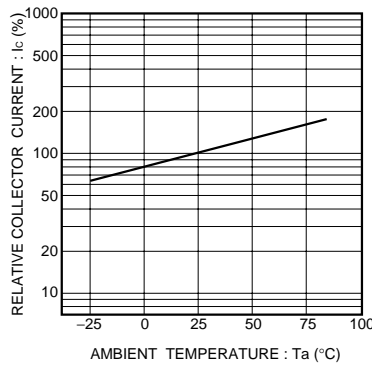


Fig.2 Relative output vs. ambient temperature

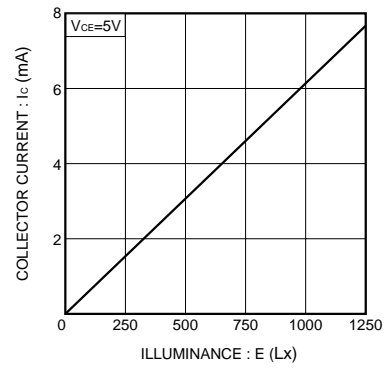


Fig.3 Light current vs. irradiance

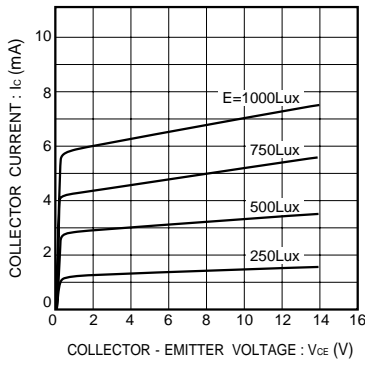


Fig.4 Output characteristics

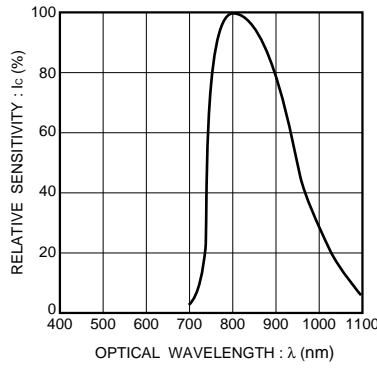


Fig.5 Spectral sensitivity

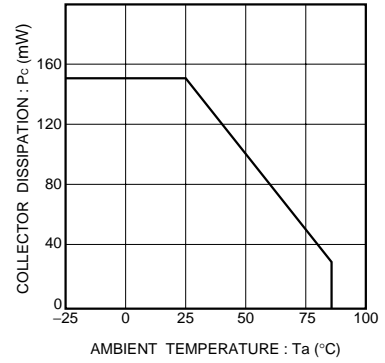


Fig.6 Collector dissipation vs. ambient temperature

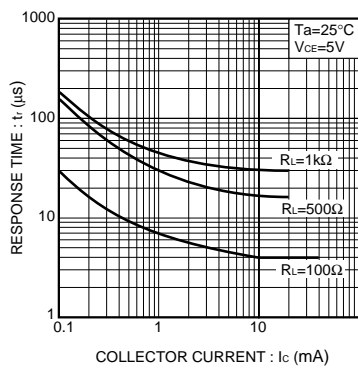


Fig.7 Response time vs. collector current

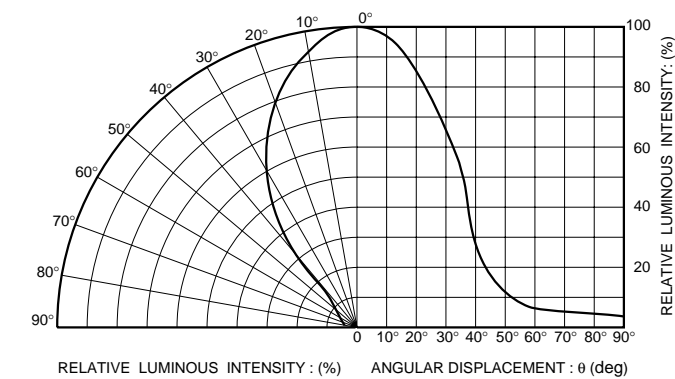


Fig.8 Directional pattern